Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	667MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360zualfh

Email: info@E-XFL.COM Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

- 10/100 Mbps Ethernet/IEEE Std. 802.3™ CDMA/CS interface through a media-independent interface (MII, RMII, RGMII)[1]
  - 1000 Mbps Ethernet/IEEE 802.3 CDMA/CS interface through a media-independent interface (GMII, RGMII, TBI, RTBI) on UCC1 and UCC2
  - 9.6-Kbyte jumbo frames
  - ATM full-duplex SAR, up to 622 Mbps (OC-12/STM-4), AAL0, AAL1, and AAL5 in accordance ITU-T I.363.5
  - ATM AAL2 CPS, SSSAR, and SSTED up to 155 Mbps (OC-3/STM-1) Mbps full duplex (with 4 CPS packets per cell) in accordance ITU-T I.366.1 and I.363.2
  - ATM traffic shaping for CBR, VBR, UBR, and GFR traffic types compatible with ATM forum TM4.1 for up to 64-Kbyte simultaneous ATM channels
  - ATM AAL1 structured and unstructured circuit emulation service (CES 2.0) in accordance with ITU-T I.163.1 and ATM Forum af-vtoa-00-0078.000
  - IMA (Inverse Multiplexing over ATM) for up to 31 IMA links over 8 IMA groups in accordance with the ATM forum AF-PHY-0086.000 (Version 1.0) and AF-PHY-0086.001 (Version 1.1)
  - ATM Transmission Convergence layer support in accordance with ITU-T I.432
  - ATM OAM handling features compatible with ITU-T I.610
  - PPP, Multi-Link (ML-PPP), Multi-Class (MC-PPP) and PPP mux in accordance with the following RFCs: 1661, 1662, 1990, 2686, and 3153
  - IP support for IPv4 packets including TOS, TTL, and header checksum processing
  - Ethernet over first mile IEEE 802.3ah
  - Shim header
  - Ethernet-to-Ethernet/AAL5/AAL2 inter-working
  - L2 Ethernet switching using MAC address or IEEE Std. 802.1P/Q™ VLAN tags
  - ATM (AAL2/AAL5) to Ethernet (IP) interworking in accordance with RFC2684 including bridging of ATM ports to Ethernet ports
  - Extensive support for ATM statistics and Ethernet RMON/MIB statistics
  - AAL2 protocol rate up to 4 CPS at OC-3/STM-1 rate
  - Packet over Sonet (POS) up to 622-Mbps full-duplex 124 MultiPHY
  - POS hardware; microcode must be loaded as an IRAM package
  - Transparent up to 70-Mbps full-duplex
  - HDLC up to 70-Mbps full-duplex
  - HDLC BUS up to 10 Mbps
  - Asynchronous HDLC
  - UART
  - BISYNC up to 2 Mbps
  - User-programmable Virtual FIFO size
  - QUICC multichannel controller (QMC) for 64 TDM channels
- One multichannel communication controller (MCC) only on the MPC8360E supporting the following:
  - 256 HDLC or transparent channels
  - 128 SS7 channels
  - Almost any combination of subgroups can be multiplexed to single or multiple TDM interfaces
- Two UTOPIA/POS interfaces on the MPC8360E supporting 124 MultiPHY each (optional 2*128 MultiPHY with extended address) and one UTOPIA/POS interface on the MPC8358E supporting 31/124 MultiPHY
- Two serial peripheral interfaces (SPI); SPI2 is dedicated to Ethernet PHY management

1.SMII or SGMII media-independent interface is not currently supported.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

This table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic		Symbol	Max Value	Unit	Notes
Core and PLL supply voltage for MPC8358 Device Part Number with Processor Frequency label of AD=266MHz and AG=400MHz & QUICC Engine Frequency label of E=300MHz & G=400MHz MPC8360 Device Part Number with Processor Frequency label of AG=400MHz and AJ=533MHz & QUICC Engine Frequency label of G=400MHz		V_{DD} & AV_{DD}	–0.3 to 1.32	V	—
Core and PLL supply voltage for MPC8360 device Part Number with Processor Frequency label of AL=667MHz and QUICC Engine Frequency label of H=500MHz		V_{DD} & AV_{DD}	–0.3 to 1.37	V	—
DDR and DDR2 DRAM I/O voltage DDR DDR2		GV_{DD}	 –0.3 to 2.75 –0.3 to 1.89	V	—
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63	V	—
PCI, local bus, DUART, system control and power management, I^2C, SPI, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I^2C, SPI, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3, 5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6

2.2.1 Power-Up Sequencing

MPC8360E/58E does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD}, LV_{DD}, and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins are actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see this figure.

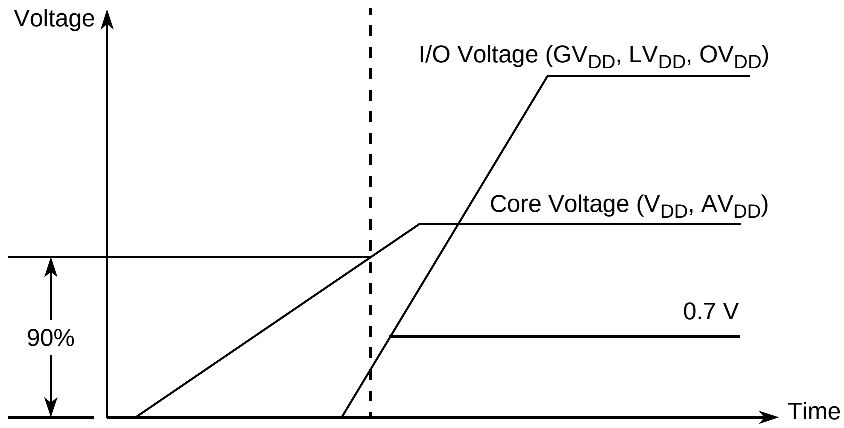


Figure 5. Power Sequencing Example

I/O voltage supplies (GV_{DD}, LV_{DD}, and OV_{DD}) do not have any ordering requirements with respect to one another.

2.2.2 Power-Down Sequencing

The MPC8360E/58E does not require the core supply voltage and I/O supply voltages to be powered down in any particular order.

3 Power Characteristics

The estimated typical power dissipation values are shown in these tables.

Table 4. MPC8360E TBGA Core Power Dissipation[1]

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
266	266	500	5.0	5.6	W	2, 3, 5
400	266	400	4.5	5.0	W	2, 3, 4
533	266	400	4.8	5.3	W	2, 3, 4
667	333	400	5.8	6.3	W	3, 6, 7, 8
500	333	500	5.9	6.4	W	3, 6, 7, 8

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	—	±10	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	μA	—
Input current (0 V ≤ V_{IN} ≤ OV_{DD})	I_{IN}	—	±10	μA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

This table provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 17. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25° C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM interface when GV_{DD}(typ) = 1.8 V.

Table 18. DDR2 SDRAM Input AC Timing Specifications for GV_{DD}(typ) = 1.8 V

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.9	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{MCK}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{MCK}$ can be shifted in ¼ applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{MCK}$, $\overline{MCS}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. Refer *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the device.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the device. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
8. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
9. In rev. 2.0 silicon, t_{DDKHMH} maximum meets the specification of 0.6 ns. In rev. 2.0 silicon, due to errata, t_{DDKHMH} minimum is –0.9 ns. Refer to Errata DDR18 in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the DDR SDRAM output timing for address skew with respect to any MCK.

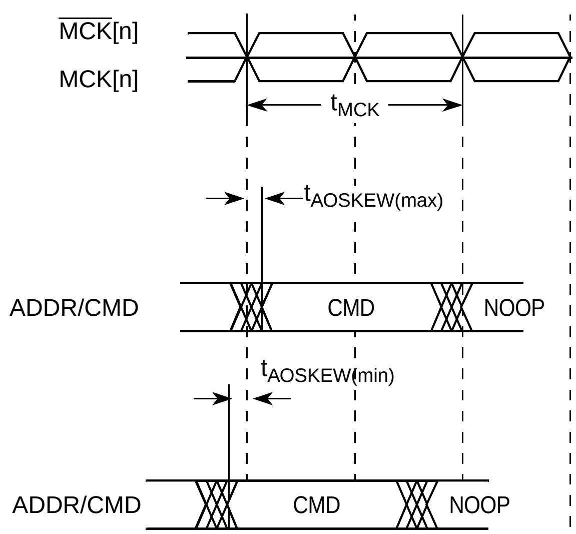


Figure 7. Timing Diagram for t_{AOSKEW} Measurement

8.2.4.2 TBI Receive AC Timing Specifications

This table provides the TBI receive AC timing specifications.

Table 34. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
PMA_RX_CLK clock period	t_{TRX}	—	16.0	—	ns	—
PMA_RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns	—
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%	—
RCG[9:0] setup time to rising PMA_RX_CLK	t_{TRDVKH}	2.5	—	—	ns	2
RCG[9:0] hold time to rising PMA_RX_CLK	t_{TRDXKH}	1.0	—	—	ns	2
RX_CLK clock rise time, V_{IL}(min) to V_{IH}(max)	t_{TRXR}	0.7	—	2.4	ns	—
RX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{TRXF}	0.7	—	2.4	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
2. Setup and hold time of even numbered RCG are measured from riding edge of PMA_RX_CLK1. Setup and hold time of odd numbered RCG are measured from riding edge of PMA_RX_CLK0.

This figure shows the TBI receive AC timing diagram.

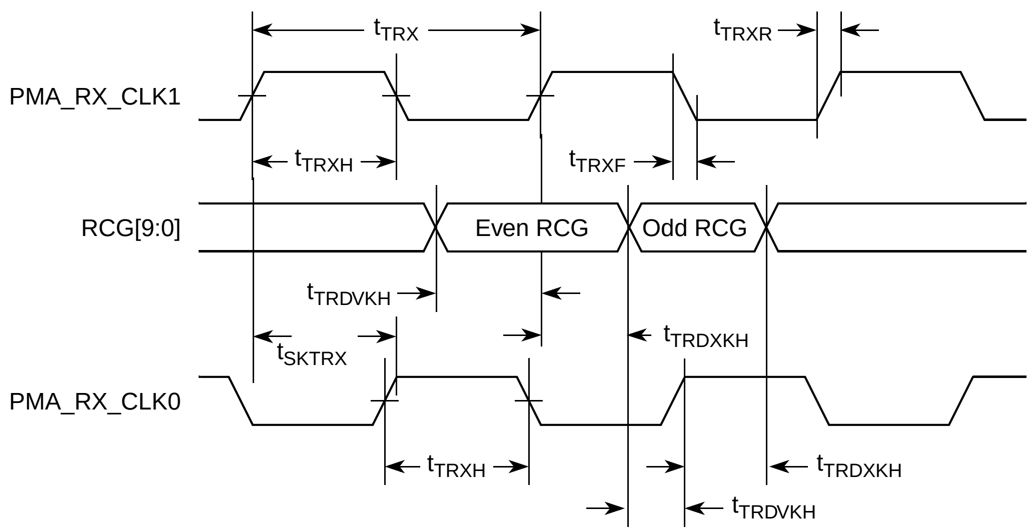


Figure 19. TBI Receive AC Timing Diagram

This figure shows the RGMII and RTBI AC timing and multiplexing diagrams.

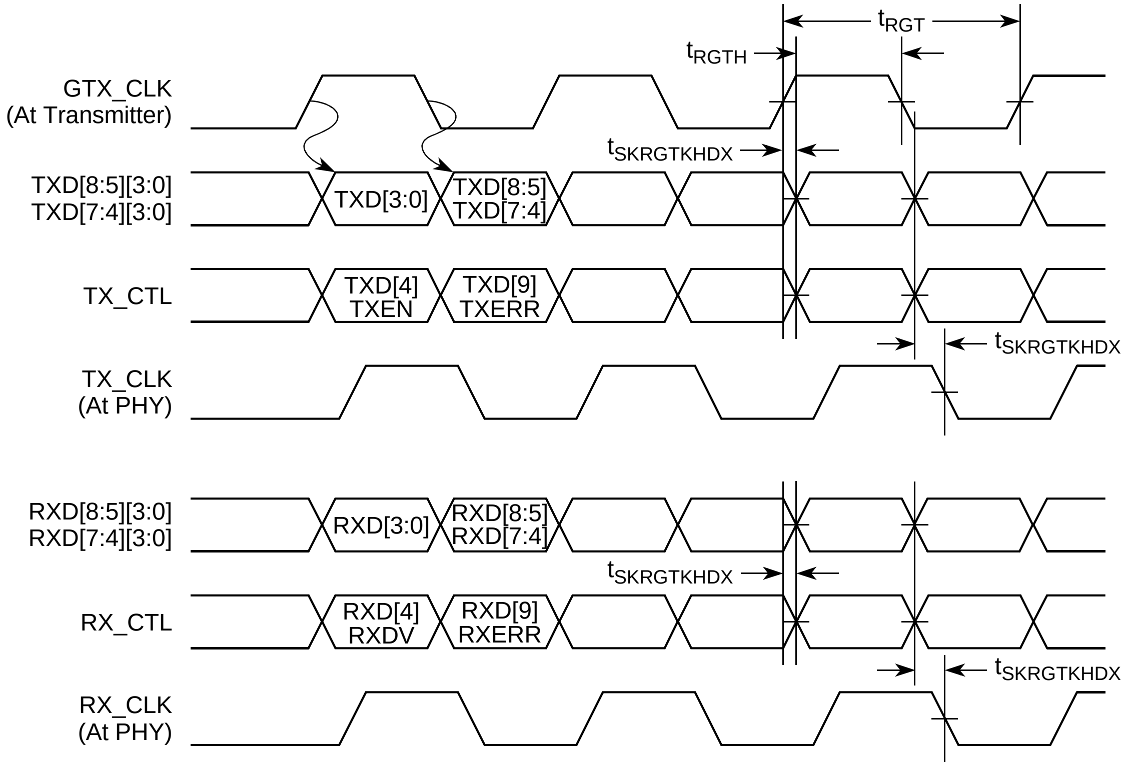


Figure 20. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI, and RTBI are specified in Section 8.1, “Three-Speed Ethernet Controller (10/100/1000 Mbps)— GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics.”

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	OV_{DD} = Min	2.10	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	0 V $\leq V_{IN} \leq OV_{DD}$		—	±10	μA

This figure shows the PCI input AC timing conditions.

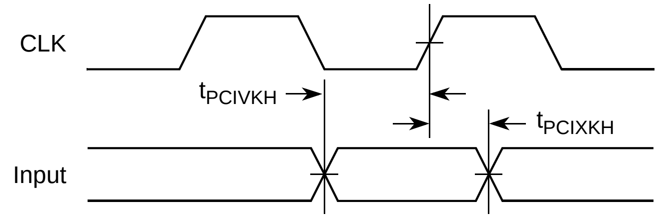


Figure 37. PCI Input AC Timing Measurement Conditions

This figure shows the PCI output AC timing conditions.

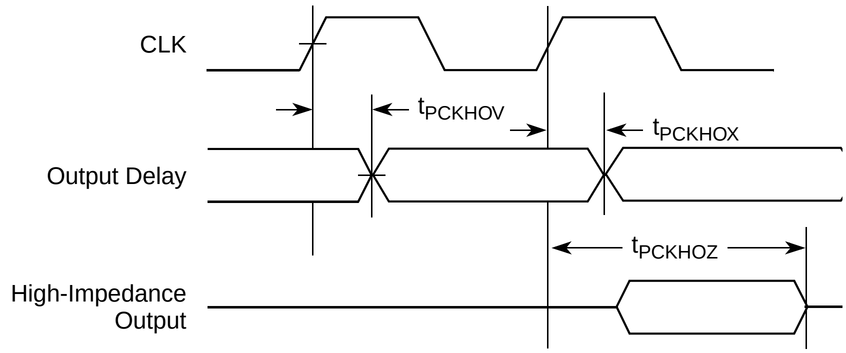


Figure 38. PCI Output AC Timing Measurement Condition

13 Timers

This section describes the DC and AC electrical specifications for the timers of the MPC8360E/58E.

13.1 Timers DC Electrical Characteristics

This table provides the DC electrical characteristics for the device timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Table 49. Timers DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V $\leq V_{IN} \leq OV_{DD}$	—	±10	μA

14.2 GPIO AC Timing Specifications

This table provides the GPIO input and output AC timing specifications.

Table 52. GPIO Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Typ	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

This figure provides the AC test load for the GPIO.

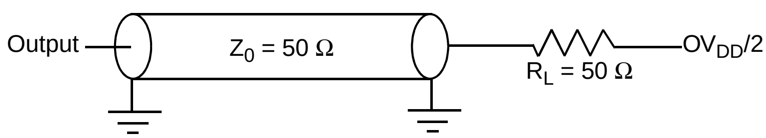


Figure 40. GPIO AC Test Load

15 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8360E/58E.

15.1 IPIC DC Electrical Characteristics

This table provides the DC electrical characteristics for the external interrupt pins of the IPIC.

Table 53. IPIC DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±10	µA
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:
1. This table applies for pins $\overline{\text{IRQ}}$[0:7], $\overline{\text{IRQ\_OUT}}$, $\overline{\text{MCP\_OUT}}$, and CE ports Interrupts.
2. $\overline{\text{IRQ\_OUT}}$ and $\overline{\text{MCP\_OUT}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

15.2 IPIC AC Timing Specifications

This table provides the IPIC input and output AC timing specifications.

Table 54. IPIC Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by any external synchronous logic. IPIC inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation when working in edge triggered mode.

16 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8360E/58E.

16.1 SPI DC Electrical Characteristics

This table provides the DC electrical characteristics for the device SPI.

Table 55. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V $\leq V_{IN} \leq OV_{DD}$	—	±10	μA

16.2 SPI AC Timing Specifications

This table and provide the SPI input and output AC timing specifications.

Table 56. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOX} t_{NIKHOV}	0.3 —	— 8	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOX} t_{NEKHOV}	2 —	— 8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	8	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns

Table 56. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

This figure provides the AC test load for the SPI.

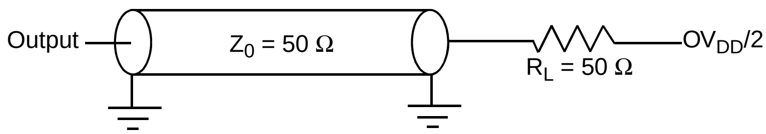
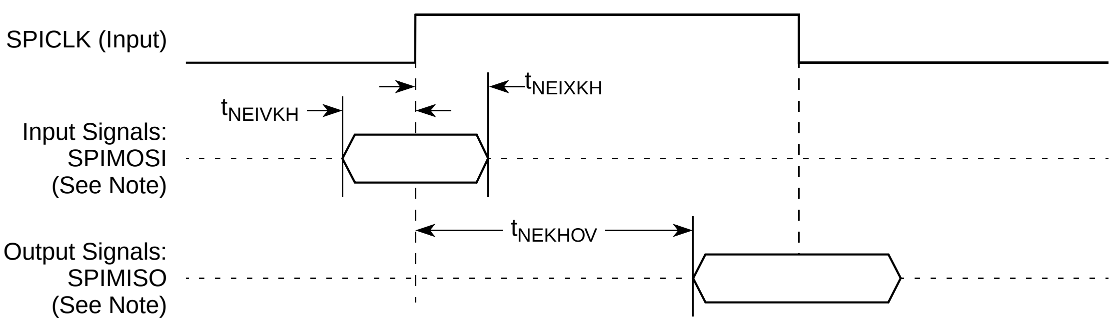


Figure 41. SPI AC Test Load

These figures represent the AC timing from Table 56. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

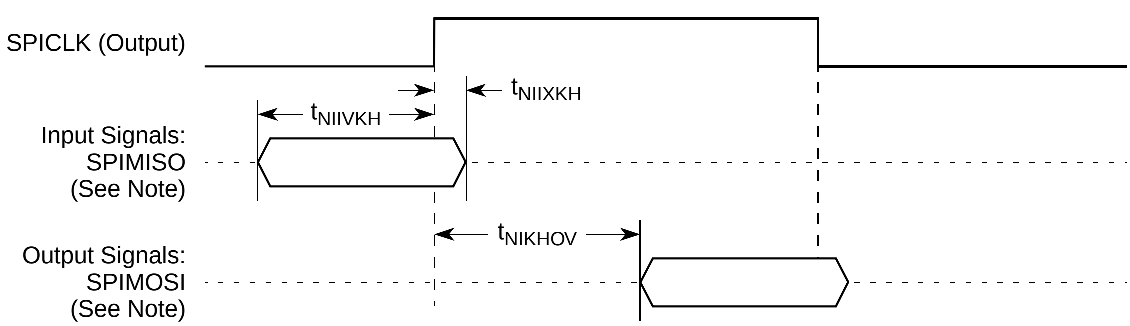
This figure shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 42. SPI AC Timing in Slave Mode (External Clock) Diagram

This figure shows the SPI timing in Master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 43. SPI AC Timing in Master Mode (Internal Clock) Diagram

17 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8360E/58E.

17.1 TDM/SI DC Electrical Characteristics

This table provides the DC electrical characteristics for the device TDM/SI.

Table 57. TDM/SI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA

17.2 TDM/SI AC Timing Specifications

This table provides the TDM/SI input and output AC timing specifications.

Table 58. TDM/SI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max[3]	Unit
TDM/SI outputs—External clock delay	t_{SEKHOV}	2	10	ns
TDM/SI outputs—External clock high impedance	t_{SEKHOX}	2	10	ns
TDM/SI inputs—External clock input setup time	t_{SEIVKH}	5	—	ns
TDM/SI inputs—External clock input hold time	t_{SEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{SEKHOX} symbolizes the TDM/SI outputs external timing (SE) for the time $t_{TDM/SI}$ memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
3. Timings are measured from the positive or negative edge of the clock, according to SIxMR [CE] and SITXCEI[TXCEIx]. Refer *MPC8360E Integrated Communications Processor Reference Manual* for more details.

This figure provides the AC test load for the TDM/SI.

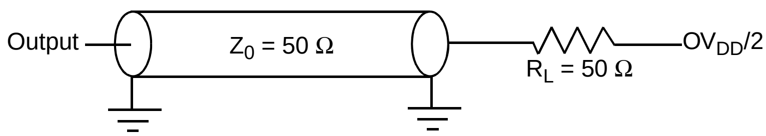


Figure 44. TDM/SI AC Test Load

Figure 45 represents the AC timing from Table 56. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

This figure shows the TDM/SI timing with external clock.

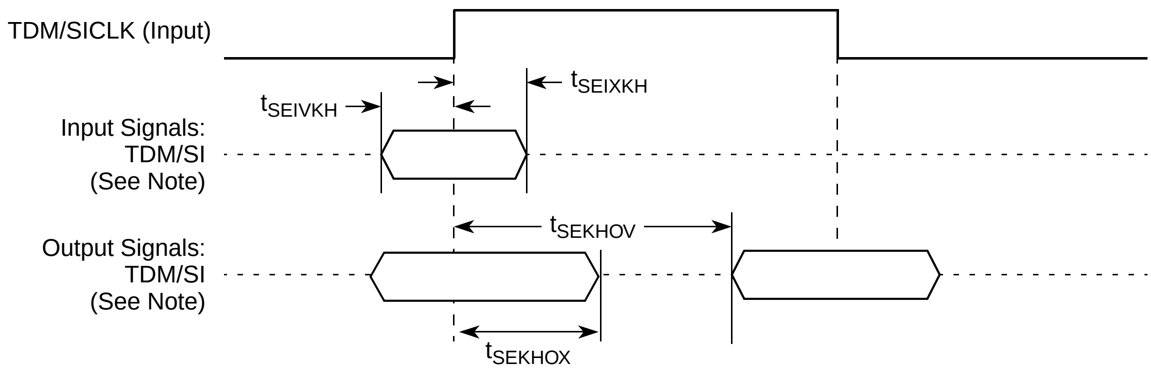


Figure 45. TDM/SI AC Timing (External Clock) Diagram

17.3 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8360E/58E.

17.4 UTOPIA/POS DC Electrical Characteristics

This table provides the DC electrical characteristics for the device UTOPIA.

Table 59. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤V_{IN} ≤OV_{DD}	—	±10	μA

17.5 UTOPIA/POS AC Timing Specifications

This table provides the UTOPIA input and output AC timing specifications.

Table 60. UTOPIA AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	11.5	ns	—
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	6	—	ns	—
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4	—	ns	3

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 63. Synchronous UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

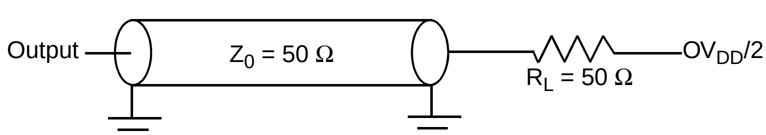


Figure 49. AC Test Load

19 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8360E/58E.

19.1 USB DC Electrical Characteristics

This table provides the DC electrical characteristics for the USB interface.

Table 64. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.4	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±10	µA

19.2 USB AC Electrical Specifications

This table describes the general timing parameters of the USB interface of the device.

Table 65. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes	Note
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz	—
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz	—
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—	2
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions	2
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions	2

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(state)(signal)}}$ for receive signals and $t_{\text{(first two letters of functional block)(state)(signal)}}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
2. Skew measurements are done at OV_{DD}/2 of the rising or falling edge of the signals.

This figure provide the AC test load for the USB.

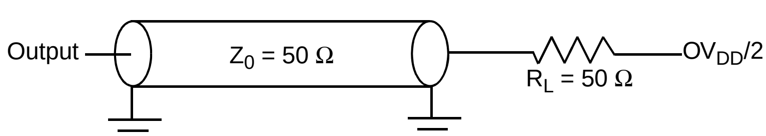


Figure 52. USB AC Test Load

Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC1_MCKE[0:1]	AL32, AU33	O	GV_{DD}	3
MEMC1_MCK[0:1]	AK37, AT37	O	GV_{DD}	—
MEMC1_MCK[2:3]/ MEMC2_MCK[0:1]	AN1, AR2	O	GV_{DD}	—
MEMC1_MCK[4:5]/ MEMC2_MCKE[0:1]	AN25, AK1	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCK}}$[0:1]	AL37, AT36	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCK}}$[2:3]/ $\overline{\text{MEMC2\_MCK}}$[0:1]	AP2, AT2	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCK}}$[4]/ MEMC2_MDM[8]	AN24	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCK}}$[5]/ MEMC2_MDQS[8]	AL1	O	GV_{DD}	—
MDIC[0:1]	AH6, AP30	I/O	GV_{DD}	10
Secondary DDR SDRAM Memory Controller Interface				
MEMC2_MECC[0:7]	AN16, AP18, AM16, AM17, AN17, AP13, AP15, AN13	I/O	GV_{DD}	—
MEMC2_MBA[0:2]	AU12, AU15, AU13	O	GV_{DD}	—
MEMC2_MA[0:14]	AT12, AP11, AT13, AT14, AR13, AR15, AR16, AT16, AT18, AT17, AP10, AR20, AR17, AR14, AR11	O	GV_{DD}	—
$\overline{\text{MEMC2\_MWE}}$	AU10	O	GV_{DD}	—
$\overline{\text{MEMC2\_MRAS}}$	AT11	O	GV_{DD}	—
$\overline{\text{MEMC2\_MCAS}}$	AU11	O	GV_{DD}	—
PCI				
PCI_INTA/$\overline{\text{IRQ\_OUT}}$/CE_PF[5]	A20	I/O	$LV_{DD}2$	2
PCI_$\overline{\text{RESET_OUT}}$/CE_PF[6]	E19	I/O	$LV_{DD}2$	—
PCI_AD[31:30]/CE_PG[31:30]	D20, D21	I/O	$LV_{DD}2$	—
PCI_AD[29:25]/CE_PG[29:25]	A24, B23, C23, E23, A26	I/O	OV_{DD}	—
PCI_AD[24]/CE_PG[24]	B21	I/O	$LV_{DD}2$	—
PCI_AD[23:0]/CE_PG[23:0]	C24, C25, D25, B25, E24, F24, A27, A28, F27, A30, C30, D30, E29, B31, C31, D31, D32, A32, C33, B33, F30, E31, A34, D33	I/O	OV_{DD}	—
PCI_C/$\overline{\text{BE}}$[3:0]/CE_PF[10:7]	E22, B26, E28, F28	I/O	OV_{DD}	—
PCI_PAR/CE_PF[11]	D28	I/O	OV_{DD}	—
$\overline{\text{PCI\_FRAME}}$/CE_PF[12]	D26	I/O	OV_{DD}	5
$\overline{\text{PCI\_TRDY}}$/CE_PF[13]	C27	I/O	OV_{DD}	5
$\overline{\text{PCI\_IRDY}}$/CE_PF[14]	C28	I/O	OV_{DD}	5
$\overline{\text{PCI\_STOP}}$/CE_PF[15]	B28	I/O	OV_{DD}	5

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
CE_PB[0:27]	AE2, AE1, AD5, AD3, AD2, AC6, AC5, AC4, AC2, AC1, AB5, AB4, AB3, AB1, AA6, AA4, AA2, Y6, Y4, Y3, Y2, Y1, W6, W5, W2, V5, V3, V2	I/O	OV_{DD}	—
CE_PC[0:1]	V1, U6	I/O	OV_{DD}	
CE_PC[2:3]	C16, A15	I/O	$LV_{DD}1$	—
CE_PC[4:6]	U4, U3, T6	I/O	OV_{DD}	—
CE_PC[7]	C19	I/O	$LV_{DD}2$	—
CE_PC[8:9]	A4, C5	I/O	$LV_{DD}0$	—
CE_PC[10:30]	T5, T4, T2, T1, R5, R3, R1, C11, D12, F13, B10, C10, E12, A9, B8, D10, A14, E15, B14, D15, AH2	I/O	OV_{DD}	—
CE_PD[0:27]	E11, D9, C8, F11, A7, E9, C7, A6, F10, B6, D7, E8, B5, A5, C2, E4, F5, B1, D2, G5, D1, E2, H6, F3, E1, F2, G3, H4	I/O	OV_{DD}	—
CE_PE[0:31]	K3, J2, F1, G2, J5, H3, G1, H2, K6, J3, K5, K4, L6, P6, P4, P3, P1, N4, N5, N2, N1, M2, M3, M5, M6, L1, L2, L4, E14, C13, C14, B13	I/O	OV_{DD}	—
CE_PF[0:3]	F14, D13, A12, A11	I/O	OV_{DD}	—
Clocks				
PCI_CLK_OUT[0]/CE_PF[26]	B22	I/O	$LV_{DD}2$	—
PCI_CLK_OUT[1:2]/CE_PF[27:28]	D22, A23	I/O	OV_{DD}	—
CLKIN	E37	I	OV_{DD}	—
PCI_CLOCK/PCI_SYNC_IN	M36	I	OV_{DD}	—
PCI_SYNC_OUT/CE_PF[29]	D37	I/O	OV_{DD}	3
JTAG				
TCK	K33	I	OV_{DD}	—
TDI	K34	I	OV_{DD}	4
TDO	H37	O	OV_{DD}	3
TMS	J36	I	OV_{DD}	4
$\overline{\text{TRST}}$	L32	I	OV_{DD}	4
Test				
TEST	L35	I	OV_{DD}	7
$\overline{\text{TEST\_SEL}}$	AU34	I	GV_{DD}	10
PMC				
$\overline{\text{QUIESCE}}$	B36	O	OV_{DD}	—
System Control				

Table 70. System PLL Multiplication Factors (continued)

RCWL[SPMF]	System PLL Multiplication Factor
1100	× 12
1101	× 13
1110	× 14
1111	× 15

The RCWL[SVCOD] denotes the system PLL VCO internal frequency as shown in this table.

Table 71. System PLL VCO Divider

RCWL[SVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider must be set properly so that the system VCO frequency is in the range of 600–1400 MHz.

The system VCO frequency is derived from the following equations:

- *csb_clk* = {PCI_SYNC_IN × (1 + CFG_CLKIN_DIV)} × SPMF
- System VCO Frequency = *csb_clk* × VCO divider (if both RCWL[DDRCM] and RCWL[LBCM] are cleared) OR
- System VCO frequency = 2 × *csb_clk* × VCO divider (if either RCWL[DDRCM] or RCWL[LBCM] are set).

As described in Section 21, “Clocking,” the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). This table shows the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 72. CSB Frequency Options

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk*: Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2:1				133
Low	0011	3:1			100	200
Low	0100	4:1		100	133	266
Low	0101	5:1		125	166	333

21.3 QUICC Engine Block PLL Configuration

The QUICC Engine block PLL is controlled by the RCWL[CEPMF], RCWL[CEPDF], and RCWL[CEVCOD] parameters. This table shows the multiplication factor encodings for the QUICC Engine block PLL.

Table 74. QUICC Engine Block PLL Multiplication Factors

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
00000	0	× 16
00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4
00101	0	× 5
00110	0	× 6
00111	0	× 7
01000	0	× 8
01001	0	× 9
01010	0	× 10
01011	0	× 11
01100	0	× 12
01101	0	× 13
01110	0	× 14
01111	0	× 15
10000	0	× 16
10001	0	× 17
10010	0	× 18
10011	0	× 19
10100	0	× 20
10101	0	× 21
10110	0	× 22
10111	0	× 23
11000	0	× 24
11001	0	× 25
11010	0	× 26
11011	0	× 27
11100	0	× 28

Table 74. QUICC Engine Block PLL Multiplication Factors (continued)

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
11101	0	× 29
11110	0	× 30
11111	0	× 31
00011	1	× 1.5
00101	1	× 2.5
00111	1	× 3.5
01001	1	× 4.5
01011	1	× 5.5
01101	1	× 6.5
01111	1	× 7.5
10001	1	× 8.5
10011	1	× 9.5
10101	1	× 10.5
10111	1	× 11.5
11001	1	× 12.5
11011	1	× 13.5
11101	1	× 14.5

Note:

1. Reserved modes are not listed.

The RCWL[CEVCOD] denotes the QUICC Engine Block PLL VCO internal frequency as shown in this table.

Table 75. QUICC Engine Block PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine block VCO frequency is in the range of 600–1400 MHz. The QUICC Engine block frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine block frequencies should be selected according to the performance requirements.